Diode Semiconductor Device - Page 1 of 1



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Incl	osure Material:
	ss and metal
Ove	erall Length:
0.37	75 inches
Ove	erall Diameter:
0.42	24 inches
Μοι	unting Facility Quantity:
1	
Μοι	unting Method:
Thre	eaded stud
Fea	tures Provided:
Her	metically sealed case
Ονε	erall Width Across Flats:
0.43	38 inches
Thr	ead Size:
0.19	00 inches
Sen	niconductor Material:
Silic	con
Vol	tage Rating In Volts Per Characteristic:
100	.0 reverse voltage, peak
Cur	rent Rating Per Characteristic:
500	.00 microamperes forward current, average major
Max	kimum Operating Tempurature Per Measurement Point:
190	.0 degrees celsius junction
Thr	ead Series Designator:
Unf	
Ter	minal Type And Quantity:
	readed stud and 1 tab, solder lug
She	If Life:
N/a	
Uni	t Of Measure:
Den	nilitarization:
No	
Fiig	:
A11	0a0